

**Features**

- $V_{DS} (V) = 55V$
- $I_D = 44A (V_{GS}=10V)$
- $R_{DS(ON)} < 27m\Omega (V_{GS} = 10V)$

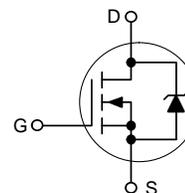
**Description**

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.

- Ultra Low On-Resistance
- Fast Switching
- Fully Avalanche Rated
- Lead-Free



1.G 2.D 3.S  
TO-252(DPAK) top view



N-Channel

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	44 <sup>⑤</sup>	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	31 <sup>⑤</sup>	
$I_{DM}$	Pulsed Drain Current <sup>①⑦</sup>	160	
$P_D @ T_C = 25^\circ C$	Power Dissipation	107	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy <sup>②⑦</sup>	210	mJ
$I_{AR}$	Avalanche Current <sup>①⑦</sup>	25	A
$E_{AR}$	Repetitive Avalanche Energy <sup>①⑦</sup>	11	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ <sup>③</sup>	5.0	V/ns
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 175	°C
$T_{STG}$			
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case		1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)		50	
$R_{\theta JA}$	Junction-to-Ambient		110	

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	55			V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient		0.055		V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance			27	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 26A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0		4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
g <sub>fs</sub>	Forward Transconductance	17			S	V <sub>DS</sub> = 25V, I <sub>D</sub> = 25A ⑦
I <sub>DSS</sub>	Drain-to-Source Leakage Current			25	μA	V <sub>DS</sub> = 55V, V <sub>GS</sub> = 0V
				250		V <sub>DS</sub> = 44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage			100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage			-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge			65	nC	I <sub>D</sub> = 25A
Q <sub>gs</sub>	Gate-to-Source Charge			12		V <sub>DS</sub> = 44V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge			27		V <sub>GS</sub> = 10V, See Fig. 6 and 13 ④ ⑦
t <sub>d(on)</sub>	Turn-On Delay Time		7.3		ns	V <sub>DD</sub> = 28V
t <sub>r</sub>	Rise Time		69			I <sub>D</sub> = 25A
t <sub>d(off)</sub>	Turn-Off Delay Time		47			R <sub>G</sub> = 12Ω
t <sub>f</sub>	Fall Time		60			R <sub>D</sub> = 1.1Ω, See Fig. 10 ④ ⑦
L <sub>D</sub>	Internal Drain Inductance		4.5		nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑥
L <sub>S</sub>	Internal Source Inductance		7.5			
C <sub>iss</sub>	Input Capacitance		1300		pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance		410			V <sub>DS</sub> = 25V
C <sub>rss</sub>	Reverse Transfer Capacitance		150			f = 1.0MHz, See Fig. 5 ⑦

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)			44 ⑤	A	MOSFET symbol showing the integral reverse p-n junction diode.
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ① ⑦			160		
V <sub>SD</sub>	Diode Forward Voltage			1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 22A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time		65	98	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 25A
Q <sub>rr</sub>	Reverse Recovery Charge		160	240	nC	di/dt = 100A/μs ④ ⑦
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② V<sub>DD</sub> = 25V, starting T<sub>J</sub> = 25°C, L = 470μH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 25A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ 25A, di/dt ≤ 320A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ Calculated continuous current based on maximum allowable junction temperature; Package limitation current = 20A
- ⑥ This is applied for I-PAK, L<sub>s</sub> of D-PAK is measured between lead and center of die contact
- ⑦ Uses IRFZ44N data and test conditions

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

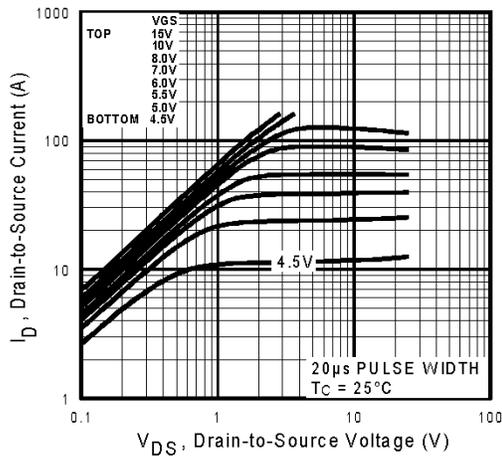


Fig 1. Typical Output Characteristics

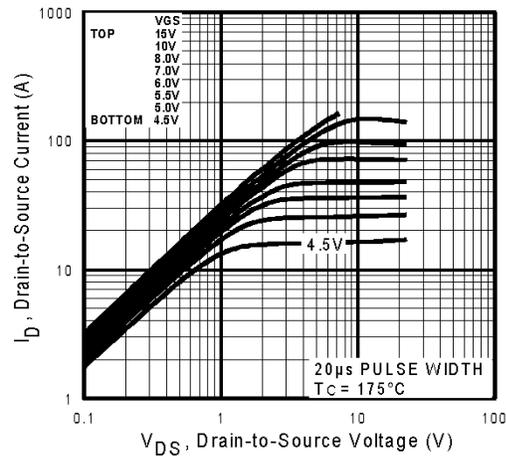


Fig 2. Typical Output Characteristics

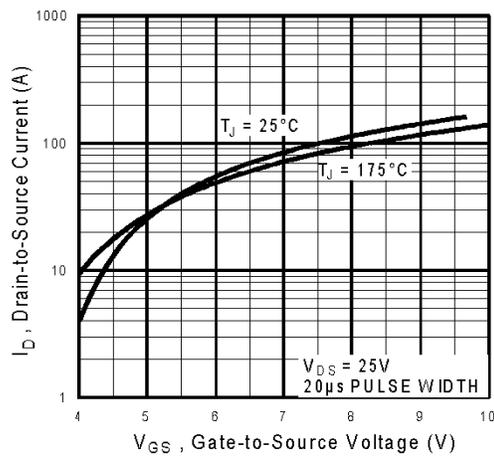


Fig 3. Typical Transfer Characteristics

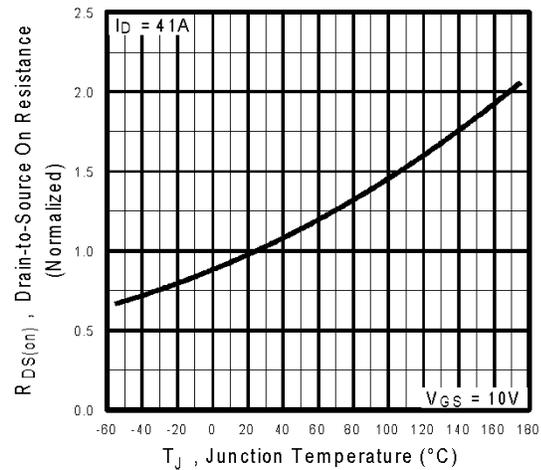
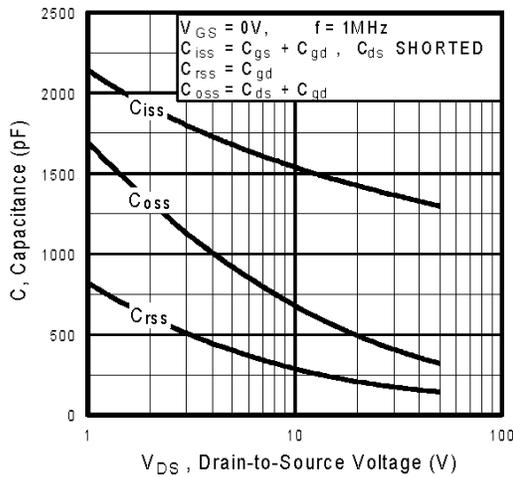
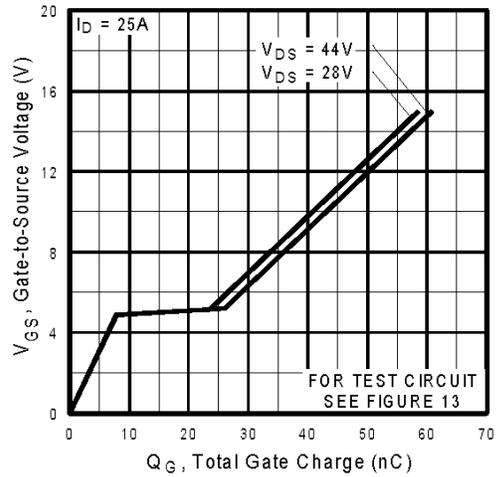


Fig 4. Normalized On-Resistance Vs. Temperature

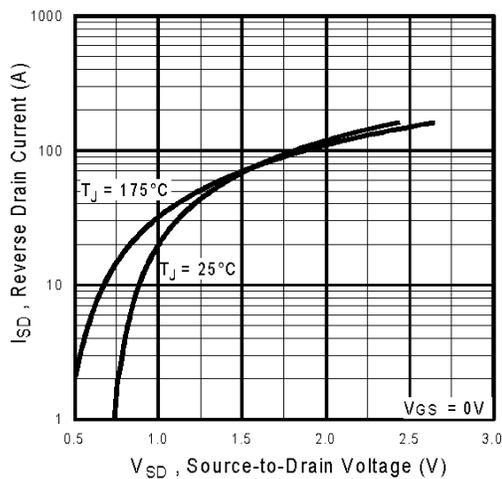
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



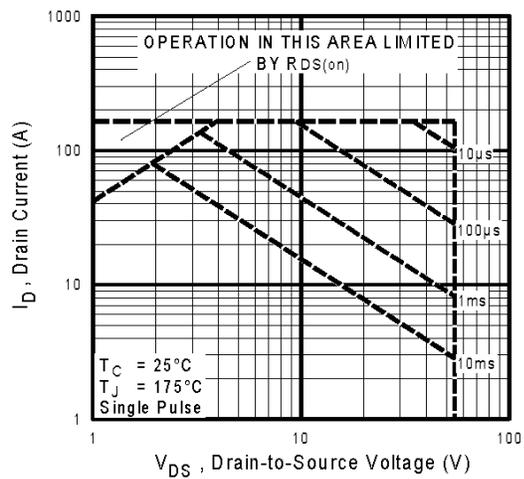
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



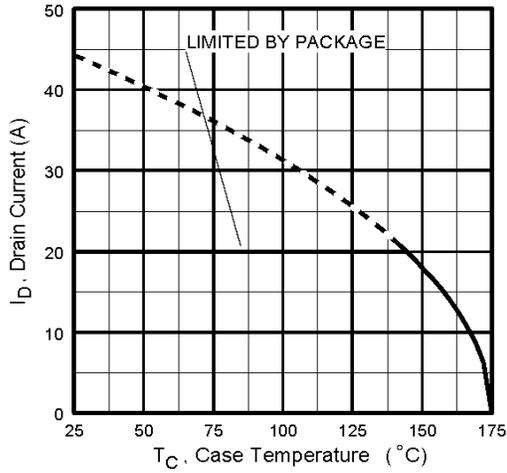
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



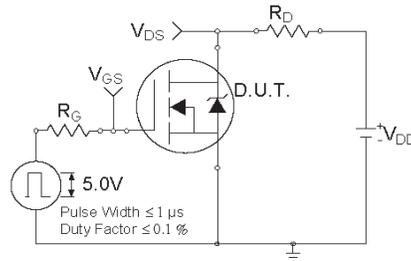
**Fig 7.** Typical Source-Drain Diode Forward Voltage



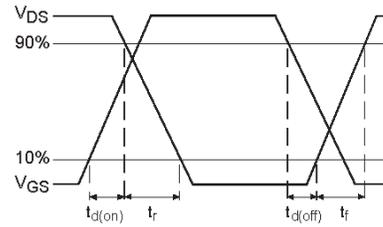
**Fig 8.** Maximum Safe Operating Area



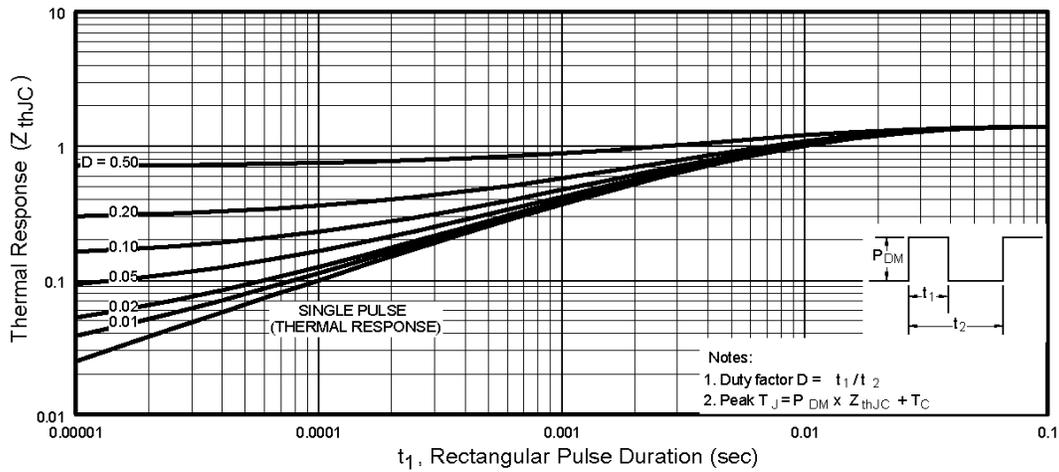
**Fig 9.** Maximum Drain Current Vs. Case Temperature



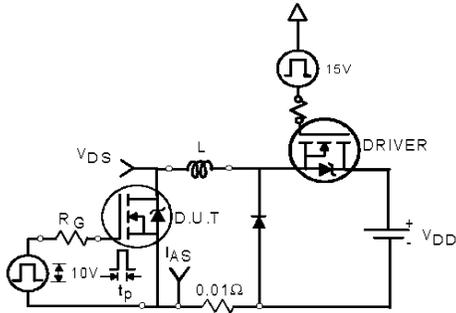
**Fig 10a.** Switching Time Test Circuit



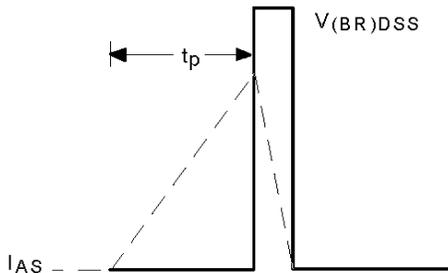
**Fig 10b.** Switching Time Waveforms



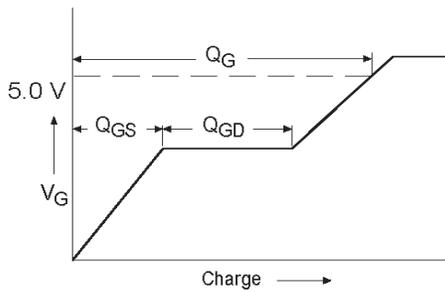
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



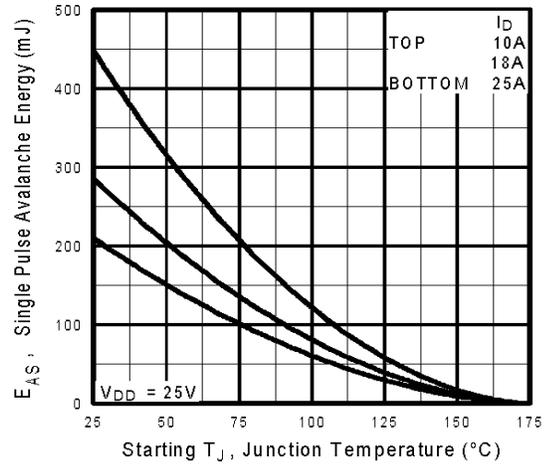
**Fig 12a.** Unclamped Inductive Test Circuit



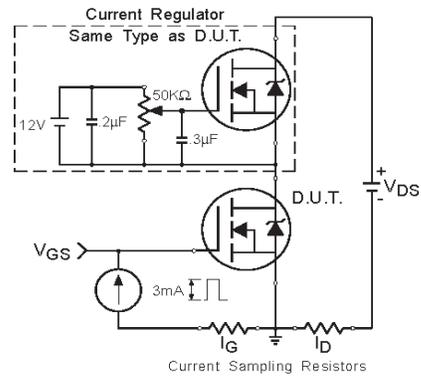
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform

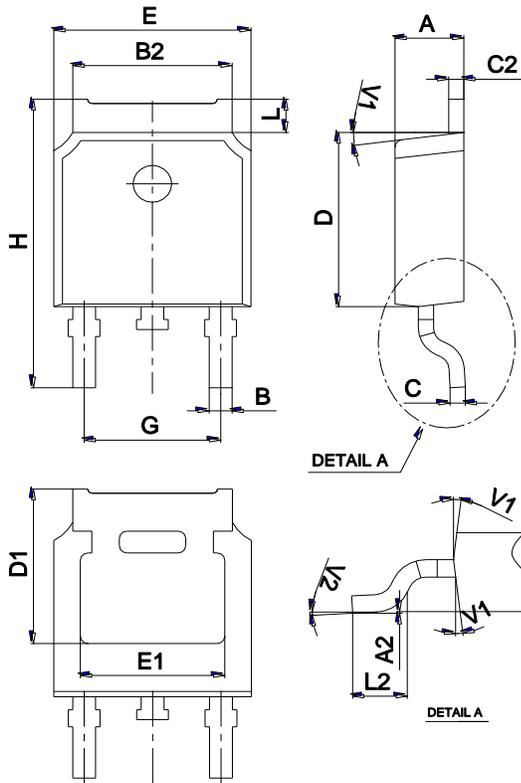


**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



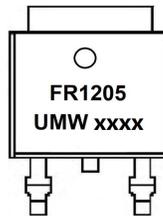
**Fig 13b.** Gate Charge Test Circuit

Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRFR1205TR	TO-252	2500	Tape and reel